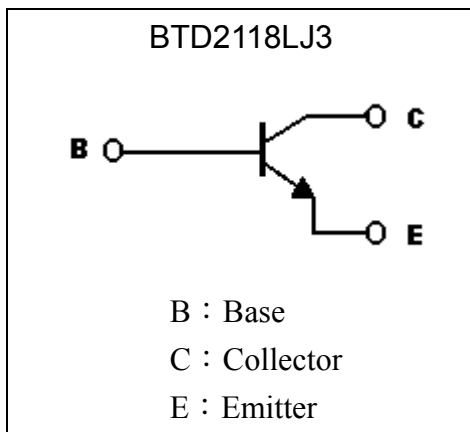
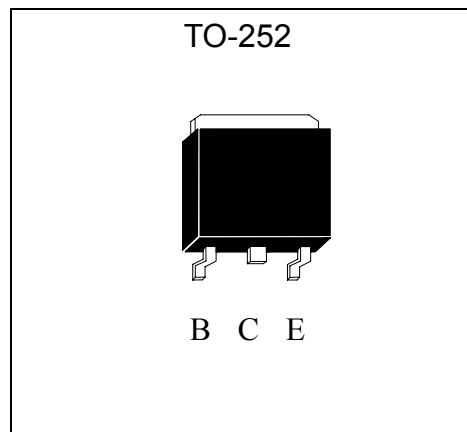


Low Vcesat NPN Epitaxial Planar Transistor

BTD2118LJ3

Features

- Low $V_{CE(sat)}$, $V_{CE(sat)}=0.25$ V (typical), at $I_C / I_B = 3A / 0.1A$
- Excellent DC current gain characteristics
- Complementary to BTB1412LJ3
- Pb-free package

Symbol

Outline

Absolute Maximum Ratings ($T_a=25^\circ\text{C}$)

Parameter	Symbol	Limits	Unit
Collector-Base Voltage	V_{CBO}	40	V
Collector-Emitter Voltage	V_{CEO}	15	V
Emitter-Base Voltage	V_{EBO}	6	V
Collector Current (DC)	I_C	5	A
Collector Current (Pulse)	I_{CP}	8 (Note 1)	A
Power Dissipation	$P_D(T_A=25^\circ\text{C})$	1	W
	$P_D(T_C=25^\circ\text{C})$	10	W
Junction Temperature	T_j	150	$^\circ\text{C}$
Storage Temperature	T_{stg}	-55~+150	$^\circ\text{C}$

Note : 1. Single Pulse $P_w \leq 350\mu\text{s}$, Duty $\leq 2\%$.

**Characteristics (Ta=25°C)**

Symbol	Min.	Typ.	Max.	Unit	Test Conditions
BV _{CBO}	40	-	-	V	I _C =50μA, I _B =0
BV _{CEO}	15	-	-	V	I _C =1mA, I _B =0
BV _{EBO}	6	-	-	V	I _E =50μA, I _C =0
I _{CBO}	-	-	0.1	μA	V _{CB} =40V, I _E =0
I _{EBO}	-	-	0.1	μA	V _{EB} =5V, I _C =0
*V _{CE(sat)}	-	0.25	0.5	V	I _C =3A, I _B =0.1A
*h _{FE1}	180	-	820	-	V _{CE} =2V, I _C =500mA
*h _{FE2}	160	-	-	-	V _{CE} =2V, I _C =2A
f _T	-	150	-	MHz	V _{CE} =6V, I _C =50mA, f=200MHz
C _{ob}	-	-	50	pF	V _{CB} =20V, I _E =0A, f=1MHz

*Pulse Test : Pulse Width ≤380μs, Duty Cycle≤2%

Classification Of h_{FE1}

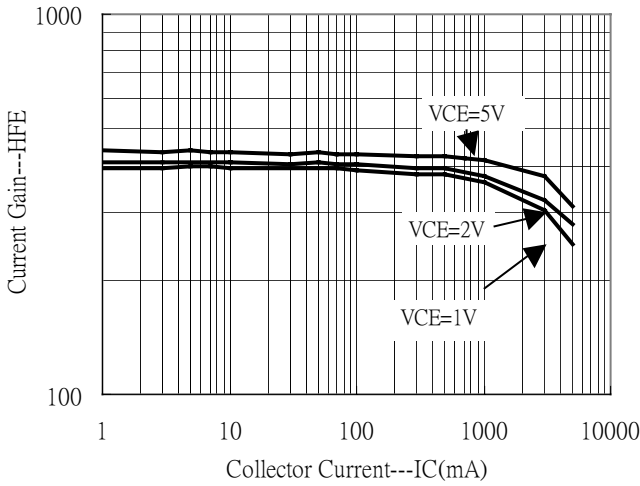
Rank	R	S	T
Range	180~390	270~560	390~820

Ordering Information

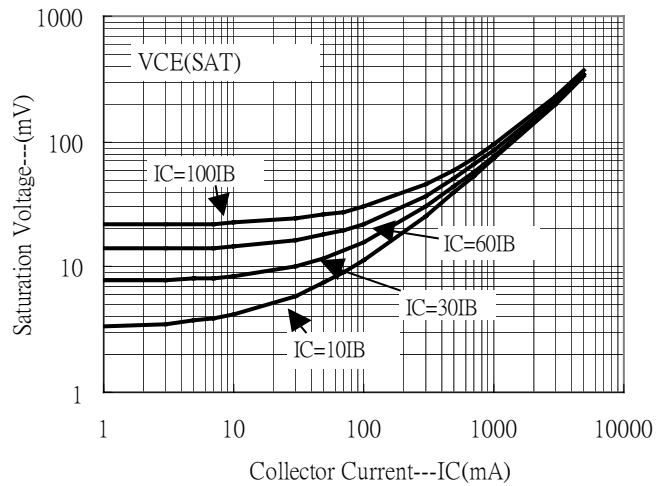
Device	Package	Shipping	Marking
BTD2118LJ3	TO-252 (Pb-free)	2500 pcs / Tape & Reel	2118L

Characteristic Curves

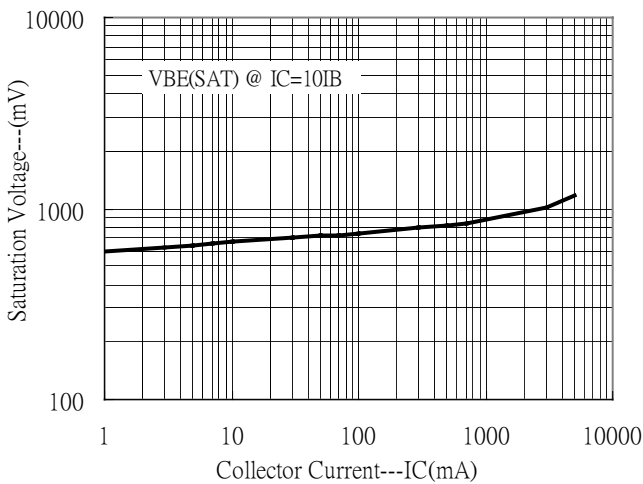
Current Gain vs Collector Current



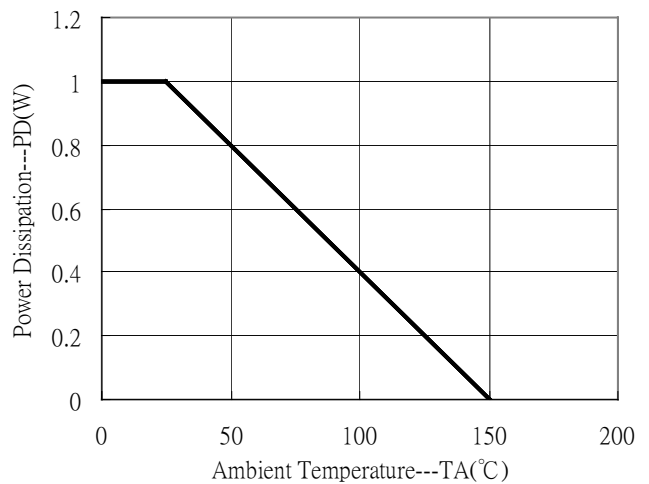
Saturation Voltage vs Collector Current



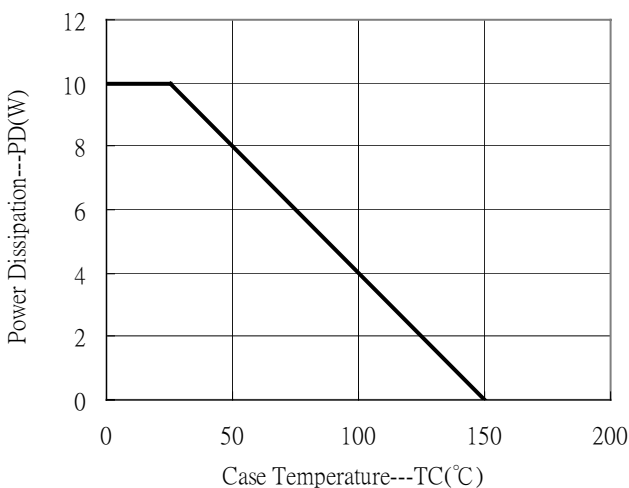
Saturation Voltage vs Collector Current



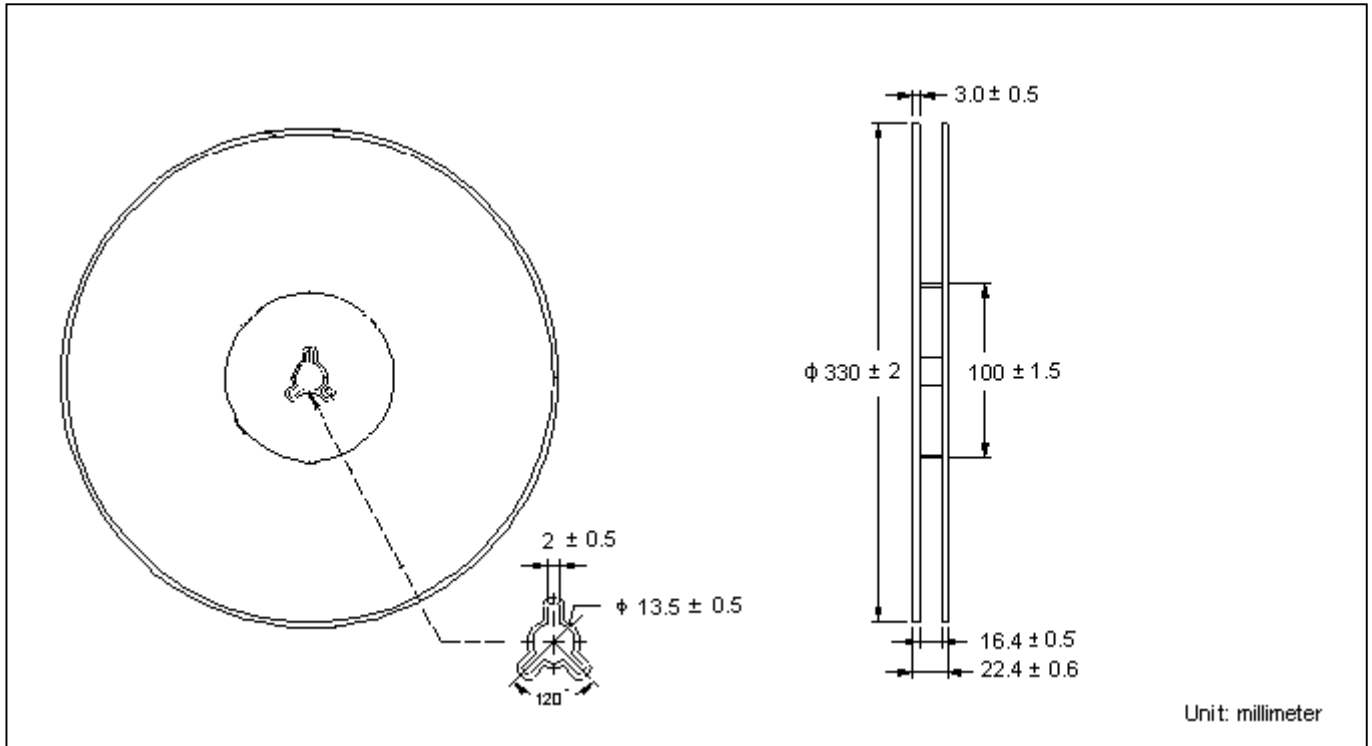
Power Derating Curve



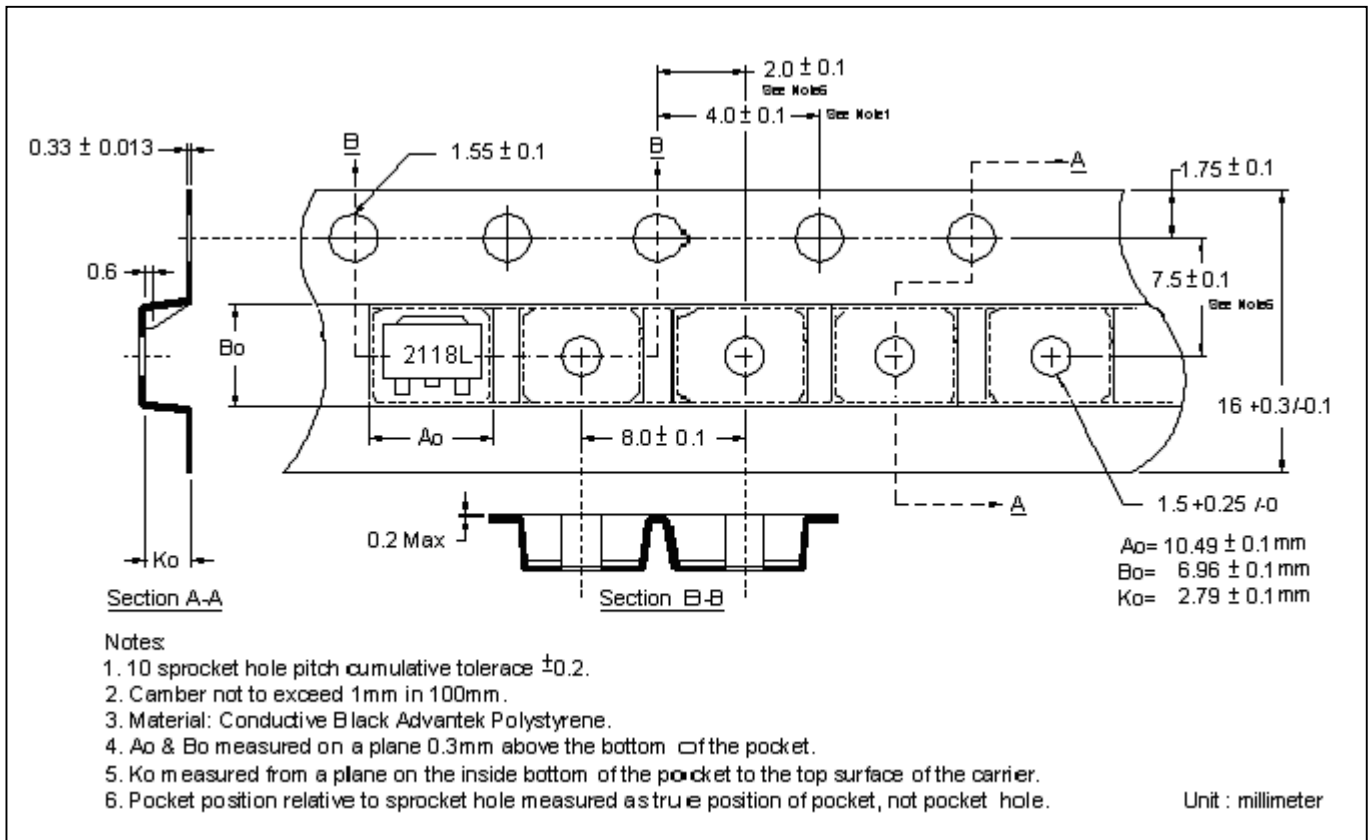
Power Derating Curve



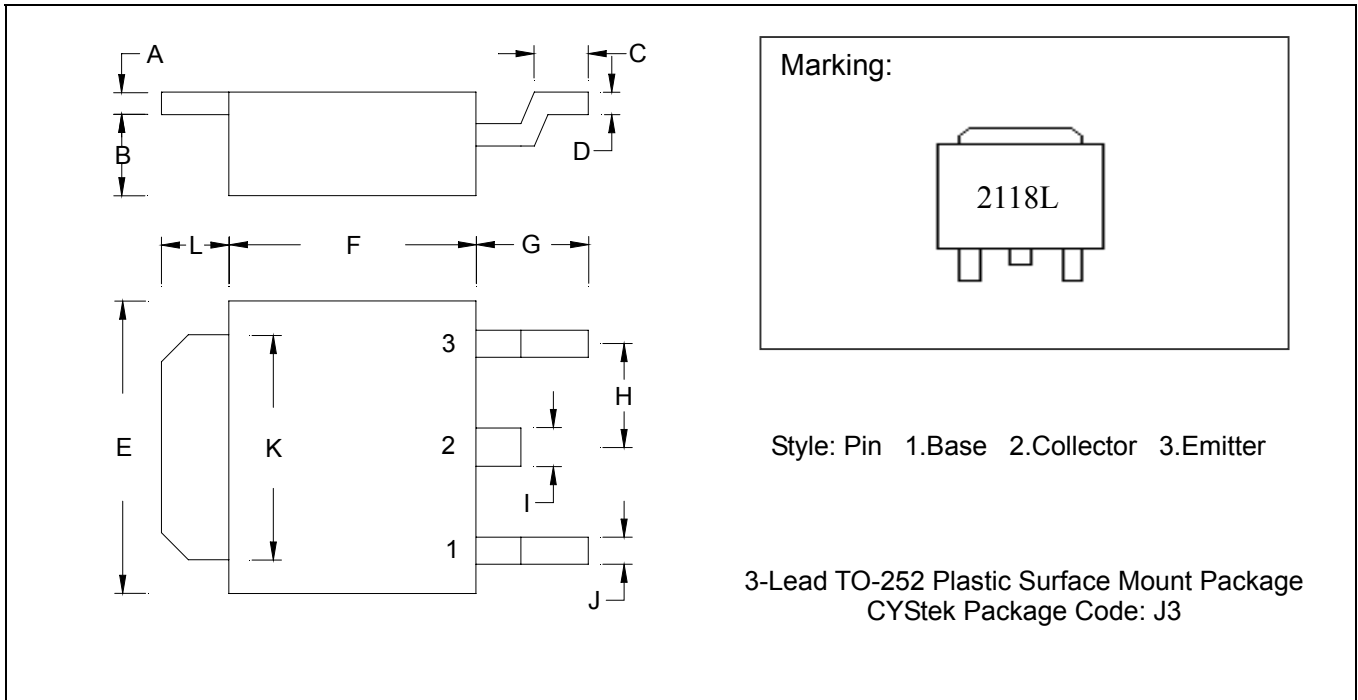
Reel Dimension



Carrier Tape Dimension



TO-252 Dimension



Style: Pin 1.Base 2.Collector 3.Emitter

3-Lead TO-252 Plastic Surface Mount Package
 CYStek Package Code: J3

*: Typical

DIM	Inches		Millimeters		DIM	Inches		Millimeters	
	Min.	Max.	Min.	Max.		Min.	Max.	Min.	Max.
A	0.0177	0.0217	0.45	0.55	G	0.0866	0.1102	2.20	2.80
B	0.0650	0.0768	1.65	1.95	H	-	*0.0906	-	*2.30
C	0.0354	0.0591	0.90	1.50	I	-	0.0354	-	0.90
D	0.0177	0.0236	0.45	0.60	J	-	0.0315	-	0.80
E	0.2520	0.2677	6.40	6.80	K	0.2047	0.2165	5.20	5.50
F	0.2125	0.2283	5.40	5.80	L	0.0551	0.0630	1.40	1.60

Notes: 1.Controlling dimension: millimeters.
 2.Maximum lead thickness includes lead finish thickness, and minimum lead thickness is the minimum thickness of base material.
 3.If there is any question with packing specification or packing method, please contact your local CYStek sales office.

Material:

- Lead: 42 Alloy; solder plating
- Mold Compound: Epoxy resin family, flammability solid burning class: UL94V-0

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